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# AN79Lxx/AN79LxxM Series

# 3-pin negative output voltage regulator (100 mA type)

### Overview

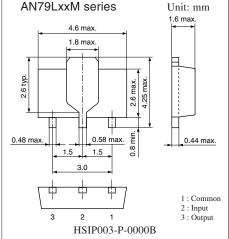
The AN79Lxx series and the AN79LxxM series are 3-pin, fixed negative output type monolithic voltage regulators.

Stabilized fixed output voltage is obtained from unstable DC input voltage without using any external components. 12 types of output voltage are available: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V and -24V. They can be used widely in power circuits with current capacity of up to 100mA.

#### Features

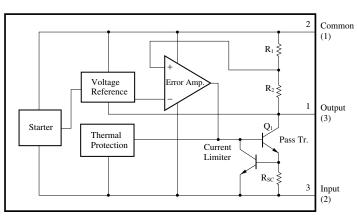
- No external components
- Output voltage: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V, -24V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit

# AN79Lxx series Unit: mm 4.0±0.2 0.6±0.15 0.43<sup>0.1</sup>/<sub>0.05</sub> 0.43<sup>0.1</sup>/<sub>0.05</sub> 1: Output 2: Common 3: Intput SSIP003-P-0000



# Note) The packages (SSIP003-P-0000 and HSIP003-P-0000B) of this product will be changed to lead-free type (SSIP003-P-0000S and HSIP003-P-0000Q). See the new package dimensions section later of this datasheet.

# ■ Block Diagram (AN79Lxx series)



Note) The number in ( ) shows the pin number for the AN79LxxM series.

# ■ Absolute Maximum Ratings at $T_a = 25$ °C

Parameter		Symbol	Rating	Unit
Input voltage		V	-35 * <sub>1</sub>	V
		$V_{I}$	-40 * <sup>2</sup>	V
Power dissipation		$P_{\mathrm{D}}$	650 *3	mW
Operating ambient tem	Operating ambient temperature		-20 to +80	°C
C4	AN79Lxx series	T	-55 to +150	90
Storage temperature	AN79LxxM series	$T_{stg}$	-55 to +125	°C

<sup>\*1</sup> AN79L04, AN79L05/M, AN79L06, AN79L07/M, AN79L08/M, AN79L09/M, AN79L10/M, AN79L12/M, AN79L15/M, AN79L18

# ■ Electrical Characteristics at T<sub>a</sub> = 25°C

# • AN79L04 (-4V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$V_{0}$	$T_j = 25^{\circ}C$	-3.84	-4	-4.16	V
Output voltage tolerance	$V_{0}$	$V_I = -7 \text{ to } -19V, I_O = 1 \text{ to } 70\text{mA}$	-3.8		-4.2	V
Line regulation	$REG_{IN}$	$V_I = -6 \text{ to } -20 \text{V}, T_j = 25^{\circ}\text{C}$			80	mV
Line regulation	KEOIN	$V_I = -7 \text{ to } -17 \text{ V}, T_j = 25^{\circ}\text{C}$			40	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		10	60	mV
	REG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		4.5	30	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -7 \text{ to } -19 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$	_		0.1	mA
Output noise voltage	$V_{no}$	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		38		μV
Ripple rejection ratio	RR	$V_1 = -7 \text{ to } -17 \text{V}, f = 120 \text{Hz}, T_a = 25 ^{\circ}\text{C}$	55			dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$	_	200	_	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5mA$		- 0.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

<sup>\*2</sup> AN79L20, AN79L24

<sup>\*3</sup> Follow the derating curve. When T<sub>j</sub> exceeds 150°C, the internal circuit cuts off the output.

AN79LxxM series is mounted on a standard board (glass epoxy: 20mm × 20mm × t1.7mm with Cu foil of 1cm² or more).

Note 2) Unless otherwise specified,  $V_I = -9V$ ,  $I_O = 40\text{mA}$ ,  $C_I = 2\mu\text{F}$ ,  $C_O = 1\mu\text{F}$ ,  $T_i = 0$  to  $125^{\circ}\text{C}$ 

# • AN79L05, AN79L05M (-5V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$V_{0}$	$T_j = 25^{\circ}C$	-4.8	-5	-5.2	V
Output voltage tolerance	$V_{0}$	$V_I = -8 \text{ to } -20V, I_O = 1 \text{ to } 70\text{mA}$	-4.75		-5.25	V
Line regulation	REG <sub>IN</sub>	$V_I = -7 \text{ to } -21 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Line regulation	KEOIN	$V_I = -8 \text{ to } -18V, T_j = 25^{\circ}C$			50	mV
I and manufaction	REG <sub>L</sub>	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		11	60	mV
Load regulation	KEUL	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		5	30	mV
Bias current	$I_{Bias}$	$T_j = 25$ °C		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -8 \text{ to } -20 \text{V}, T_j = 25 ^{\circ}\text{C}$		_	0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to $100kHz$ , $T_a = 25$ °C		40		μV
Ripple rejection ratio	RR	$V_I = -8 \text{ to } -18V, f = 120Hz, T_a = 25^{\circ}C$	55		_	dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5mA$		- 0.4	_	mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

# • AN79L06 (-6V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-5.76	-6	-6.24	V
Output voltage tolerance	Vo	$V_I = -9 \text{ to } -21 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-5.7		-6.3	V
Line regulation	REG <sub>IN</sub>	$V_I = -8 \text{ to } -22 \text{V}, T_j = 25^{\circ}\text{C}$			120	mV
Life regulation	KEG <sub>IN</sub>	$V_I = -9 \text{ to } -19V, T_j = 25^{\circ}C$		_	60	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		12	60	mV
	REG <sub>L</sub>	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		5.5	30	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -9 \text{ to } -21 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to $100kHz$ , $T_a = 25$ °C		44		μV
Ripple rejection ratio	RR	$V_1 = -9 \text{ to } -19V, f = 120Hz, T_a = 25^{\circ}C$	55			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25$ °C		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$	_	200		mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5mA$		- 0.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_1 = -11V$ ,  $I_0 = 40\text{mA}$ ,  $C_1 = 2\mu\text{F}$ ,  $C_0 = 1\mu\text{F}$ ,  $T_j = 0$  to  $125^{\circ}\text{C}$ 

Note 2) Unless otherwise specified,  $V_I = -10V$ ,  $I_O = 40\text{mA}$ ,  $C_I = 2\mu\text{F}$ ,  $C_O = 1\mu\text{F}$ ,  $T_j = 0$  to 125°C (AN79L05) and  $T_j = 0$  to 100°C (AN79L05M)

# • AN79L07, AN79L07M (-7V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-6.72	-7	-7.28	V
Output voltage tolerance	$V_{O}$	$V_I = -10 \text{ to } -22V, I_O = 1 \text{ to } 70\text{mA}$	-6.65	_	-7.35	V
Line regulation	REG <sub>IN</sub>	$V_I = -9 \text{ to } -23 \text{V}, T_j = 25^{\circ}\text{C}$		_	140	mV
Line regulation	KEOIN	$V_I = -10 \text{ to } -20 \text{V}, T_j = 25^{\circ}\text{C}$		_	70	mV
Lord regulation	REG <sub>L</sub>	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		13	70	mV
Load regulation	KEUL	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		6	40	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -10 \text{ to } -22 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		48	_	μV
Ripple rejection ratio	RR	$V_1 = -10$ to $-20$ V, $f = 120$ Hz, $T_a = 25$ °C	54			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5mA$		- 0.5	_	mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

### AN79L08, AN79L08M (-8V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$V_{O}$	$T_j = 25^{\circ}C$	-7.68	-8	-8.32	V
Output voltage tolerance	Vo	$V_I = -11 \text{ to } -23V, I_O = 1 \text{ to } 70\text{mA}$	-7.6		-8.4	V
Line regulation	REG <sub>IN</sub>	$V_I = -10 \text{ to } -24 \text{V}, T_j = 25^{\circ}\text{C}$			160	mV
Line regulation	KEG <sub>IN</sub>	$V_I = -11 \text{ to } -21 \text{V}, T_j = 25^{\circ}\text{C}$		_	80	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		15	80	mV
	REG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		7	40	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -11 \text{ to } -23 \text{V}, T_j = 25^{\circ}\text{C}$		_	0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		52	_	μV
Ripple rejection ratio	RR	$V_I = -11$ to $-21V$ , $f = 120Hz$ , $T_a = 25$ °C	54		_	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5 \text{mA}, T_j = 0 \text{ to } 125^{\circ}\text{C}$		- 0.6		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -12V$ ,  $I_O = 40mA$ ,  $C_I = 2\mu F$ ,  $C_O = 1\mu F$ ,  $T_j = 0$  to  $125^{\circ}C$  (AN79L07) and  $T_j = 0$  to  $100^{\circ}C$  (AN79L07M)

Note 2) Unless otherwise specified,  $V_I = -14V$ ,  $I_O = 40\text{mA}$ ,  $C_I = 2\mu\text{F}$ ,  $C_O = 1\mu\text{F}$ ,  $T_j = 0$  to 125°C (AN79L08) and  $T_j = 0$  to 100°C (AN79L08M)

# • AN79L09, AN79L09M (-9V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$V_{0}$	$T_j = 25^{\circ}C$	-8.64	-9	-9.36	V
Output voltage tolerance	Vo	$V_I = -12 \text{ to } -24 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-8.55		-9.45	V
Line regulation	REGIN	$V_I = -11 \text{ to } -25 \text{V}, T_j = 25^{\circ}\text{C}$			160	mV
Line regulation	KEOIN	$V_I = -12 \text{ to } -22 \text{V}, T_j = 25^{\circ}\text{C}$		_	80	mV
I and manufaction	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		16	90	mV
Load regulation	REG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		8	50	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -12 \text{ to } -24 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz \text{ to } 100kHz, T_a = 25^{\circ}C$		58		μV
Ripple rejection ratio	RR	$V_I = -12 \text{ to } -22 \text{V}, f = 120 \text{Hz}, T_a = 25 ^{\circ}\text{C}$	53			dB
Minimum input/output voltage difference	$V_{\text{DIF}(min)}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5 \text{mA}, T_j = 0 \text{ to } 125^{\circ}\text{C}$		- 0.6	_	mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

# • AN79L10, AN79L10M (-10V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-9.6	-10	-10.4	V
Output voltage tolerance	Vo	$V_I = -13 \text{ to } -25 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-9.5		-10.5	V
Line regulation	DEC	$V_I = -12 \text{ to } -26V, T_j = 25^{\circ}C$		_	160	mV
Line regulation	REG <sub>IN</sub>	$V_I = -13 \text{ to } -23 \text{V}, T_j = 25^{\circ}\text{C}$		_	80	mV
Load regulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		17	100	mV
	REG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		9	50	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$	_	3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -13 \text{ to } -25 \text{V}, T_j = 25 ^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		65		μV
Ripple rejection ratio	RR	$V_I = -13 \text{ to } -23 \text{V}, f = 120 \text{Hz}, T_a = 25^{\circ}\text{C}$	53			dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5mA$		- 0.7		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -16V$ ,  $I_O = 40\text{mA}$ ,  $C_I = 2\mu\text{F}$ ,  $C_O = 1\mu\text{F}$ ,  $T_j = 0$  to  $125^{\circ}\text{C}$  (AN79L10) and  $T_j = 0$  to  $100^{\circ}\text{C}$  (AN79L10M)

Note 2) Unless otherwise specified,  $V_I = -15V$ ,  $I_O = 40$ mA,  $C_I = 2\mu$ F,  $C_O = 1\mu$ F,  $T_j = 0$  to 125°C (AN79L09) and  $T_j = 0$  to 100°C (AN79L09M)

# • AN79L12, AN79L12M (-12V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-11.5	-12	-12.5	V
Output voltage tolerance	Vo	$V_I = -15 \text{ to } -27 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-11.4		-12.6	V
Line recordetion	REG <sub>IN</sub>	$V_I = -14.5 \text{ to } -30 \text{V}, T_j = 25^{\circ}\text{C}$		_	200	mV
Line regulation	KEOIN	$V_I = -15 \text{ to } -25 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
I and manufaction	REG <sub>L</sub>	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		20	100	mV
Load regulation	KEUL	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		10	50	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -15 \text{ to } -27 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		75	_	μV
Ripple rejection ratio	RR	$V_I = -15 \text{ to } -25 \text{V}, f = 120 \text{Hz}, T_a = 25 ^{\circ}\text{C}$	52		_	dB
Minimum input/output voltage difference	$V_{\text{DIF}(min)}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_0 = 5mA$		- 0.8	_	mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

# • AN79L15, AN79L15M (-15V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$V_{0}$	$T_j = 25^{\circ}C$	-14.4	-15	-15.6	V
Output voltage tolerance	Vo	$V_I = -18 \text{ to } -28 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-14.25		-15.75	V
Line regulation	REG <sub>IN</sub>	$V_I = -17.5 \text{ to } -33 \text{V}, T_j = 25^{\circ}\text{C}$			200	mV
Line regulation	KEUIN	$V_I = -18 \text{ to } -28 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Load regulation	REG <sub>I</sub>	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		25	130	mV
	KEG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		12	60	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -18 \text{ to } -30 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$	_	_	0.1	mA
Output noise voltage	$V_{no}$	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		90		μV
Ripple rejection ratio	RR	$V_I = -18 \text{ to } -28 \text{V}, f = 120 \text{Hz}, T_a = 25 ^{\circ}\text{C}$	51			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5mA$		- 0.9		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}\text{C}$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -19V$ ,  $I_O = 40mA$ ,  $C_I = 2\mu F$ ,  $C_O = 1\mu F$ ,  $T_j = 0$  to  $125^{\circ}C$  (AN79L12) and  $T_j = 0$  to  $100^{\circ}C$  (AN79L12M)

Note 2) Unless otherwise specified,  $V_I = -23V$ ,  $\tilde{I}_O = 40\text{mA}$ ,  $\tilde{C}_I = 2\mu\text{F}$ ,  $C_O = 1\mu\text{F}$ ,  $T_j = 0$  to 125°C (AN79L15) and  $T_j = 0$  to 100°C (AN79L15M)

# • AN79L18 (-18V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-17.3	-18	-18.7	V
Output voltage tolerance	Vo	$V_I = -21 \text{ to } -33 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-17.1		-18.9	V
Line regulation	REG <sub>IN</sub>	$V_I = -21 \text{ to } -33 \text{V}, T_j = 25^{\circ}\text{C}$			200	mV
Line regulation	KEOIN	$V_I = -21 \text{ to } -32 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
I I	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		30	160	mV
Load regulation	REG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		15	80	mV
Bias current	$I_{\text{Bias}}$	$T_j = 25$ °C		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -21 \text{ to } -33 \text{V}, T_j = 25^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		110		μV
Ripple rejection ratio	RR	$V_I = -22 \text{ to } -32 \text{V}, f = 120 \text{Hz}, T_a = 25 ^{\circ}\text{C}$	50			dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25$ °C		0.8	_	V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$	_	200	_	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5mA$	_	-1	_	mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

# • AN79L20 (-20V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$V_{o}$	$T_j = 25$ °C	-19.2	-20	-20.8	V
Output voltage tolerance	$V_{o}$	$V_I = -23 \text{ to } -35 \text{V}, I_O = 1 \text{ to } 70 \text{mA}$	-19		-21	V
Line regulation	REG <sub>IN</sub>	$V_I = -23 \text{ to } -35 \text{V}, T_j = 25 ^{\circ}\text{C}$			200	mV
Line regulation	KEOIN	$V_I = -24 \text{ to } -34 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Lond regulation	DEC	$I_0 = 1 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		35	180	mV
Load regulation	REG <sub>L</sub>	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		17	90	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -23 \text{ to } -35 \text{V}, T_j = 25 ^{\circ}\text{C}$		_	0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		135		μV
Ripple rejection ratio	RR	$V_I = -24 \text{ to } -34 \text{V}, f = 120 \text{Hz}, T_a = 25^{\circ}\text{C}$	49			dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$T_j = 25$ °C		0.8	_	V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$	_	200	_	mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5mA$		-1		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_1 = -29V$ ,  $I_0 = 40\text{mA}$ ,  $C_1 = 2\mu\text{F}$ ,  $C_0 = 1\mu\text{F}$ ,  $T_j = 0$  to  $125^{\circ}\text{C}$ 

Note 2) Unless otherwise specified,  $V_1 = -27V$ ,  $I_0 = 40mA$ ,  $C_1 = 2\mu F$ ,  $C_0 = 1\mu F$ ,  $T_1 = 0$  to  $125^{\circ}C$ 

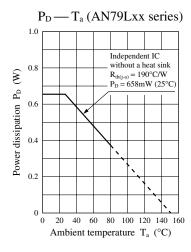
# • AN79L24 (-24V type)

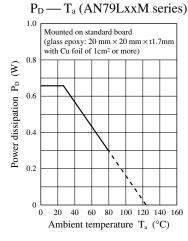
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-23	-24	-25	V
Output voltage tolerance	Vo	$V_I = -27 \text{ to } -38V, I_O = 1 \text{ to } 70\text{mA}$	-22.8		-25.2	V
Line regulation	REG <sub>IN</sub>	$V_I = -27 \text{ to } -38 \text{V}, T_j = 25 ^{\circ}\text{C}$			200	mV
		$V_I = -27 \text{ to } -37 \text{V}, T_j = 25^{\circ}\text{C}$			100	mV
Load regulation	$REG_L$	$I_0 = 1 \text{ to } 100\text{mA}, T_j = 25^{\circ}\text{C}$		40	200	mV
		$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$		20	100	mV
Bias current	$I_{Bias}$	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -27 \text{ to } -38 \text{V}, T_j = 25 ^{\circ}\text{C}$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1 \text{ to } 40\text{mA}, T_j = 25^{\circ}\text{C}$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10$ Hz to $100$ kHz, $T_a = 25$ °C		170		μV
Ripple rejection ratio	RR	$V_1 = -28 \text{ to } -38 \text{V}, f = 120 \text{Hz}, T_a = 25^{\circ}\text{C}$	49		_	dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$I_O = 5mA$	_	-1	_	mV/°C

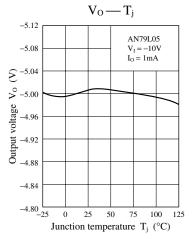
Note 1) The specified condition  $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_1 = -33V$ ,  $I_0 = 40\text{mA}$ ,  $C_1 = 2\mu\text{F}$ ,  $C_0 = 1\mu\text{F}$ ,  $T_1 = 0$  to  $125^{\circ}\text{C}$ 

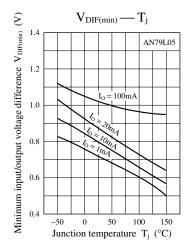
# ■ Main Characteristics

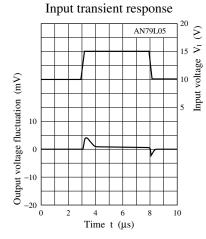


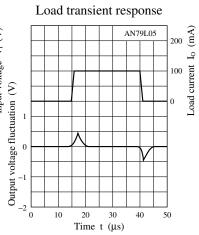


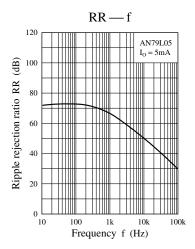


# ■ Main Characteristics (continued)

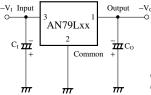








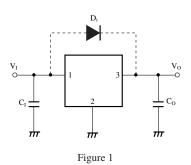
# ■ Basic Regulator Circuit



Connect  $C_I$  of  $2\mu F$  when the input line is long.  $C_O$  improves the transient response.  $1\mu F$ 

# ■ Usage Notes

## 1. Cautions for a basic circuit



 $C_{I}$ : When a wiring from a smoothing circuit to a three-pin regulator is long, it is likely to oscillate at output. A capacitor of  $0.1\mu F$  to  $0.47\mu F$  should be connected near an input pin.

 $C_{O}$ : Deadly needed to prevent from oscillation (0.33 $\mu$ F to 1.0 $\mu$ F). It is recommended to use a capacitor of a small internal impedance (ex. tantalum capacitor) when using it under a low temperature.

When any sudden change of load current is likely to occur, connect an electrolytic capacitor of  $10\mu\text{F}$  to  $100\mu\text{F}$  to improve a transitional response of output voltage.

D<sub>i</sub>: Normally unnecessary. But add it in the case that there is a residual voltage at the output capacitor Co even after switching off the supply power because a current is likely to flow into an output pin of the IC and damage the IC.

### 2. Other caution items

# 1) Short-circuit between the input pin and GND pin

If the input pin is short-circuitted to GND or is cut off when a large capacitance capacitor has been connected to the IC's load, a voltage of a capacitor connected to an output pin is applied between input/output of the IC and this likely results in damage of the IC. It is necessary, therefore, to connect a diode, as shown in figure 2, to counter the reverse bias between input/output pins.

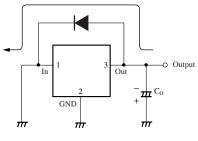
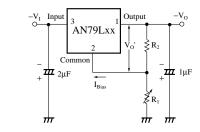


Figure 2

# 2) Floating of GND pin

If a GND pin is made floating in an operating mode, an unstabilized input voltage is outputted. In this case, a thermal protection circuit inside the IC does not normally operate. In this state, if the load is short-circuited or overloaded, it is likely to damage the IC.

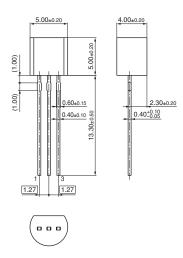
# ■ Application Circuit Example



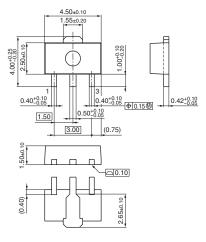
$$|V_{\mathrm{O}}| = V_{\mathrm{O}}' \left(1 + \frac{R_{1}}{R_{2}}\right) + I_{Q}R_{1}$$

Note)  $V_{\rm O}$  varies due to sample to sample variation of  $I_{\rm Bias}$  . Never fail to adjust individually with  $R_{\rm I}$  .

- New Package Dimensions (Unit: mm)
- SSIP003-P-0000S (Lead-free package)



• HSIP003-P-0000Q (Lead-free package)



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